

# **KSA1381**

### **CRT Display, Video Output**

- High Collector-Emitter Breakdown Voltage: V<sub>CEO</sub>= -300V
- Low Reverse Transfer Capacitance : C<sub>re</sub>= 2.3pF at V<sub>CB</sub> = -30V



# **PNP Epitaxial Silicon Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{CBO}$	Collector-Base Voltage	- 300	V
V <sub>CEO</sub>	Collector-Emitter Voltage	- 300	V
V <sub>EBO</sub>	Emitter-Base Voltage	- 5	V
Ic	Collector Current (DC)	- 100	mA
I <sub>CP</sub>	Collector Current (Pulse)	- 200	mA
$P_{C}$	Collector Dissipation (T <sub>C</sub> =25°C)	7	W
P <sub>C</sub>	Collector Dissipation (T <sub>a</sub> =25°C)	1.2	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = -10\mu A, I_E = 0$	- 300			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{C} = -1 \text{mA}, I_{B} = 0$	- 300			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -10\mu A, I_C = 0$	- 5			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = -200V, I_{E} = 0$			- 0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -4V, I_{C} = 0$	1.1		- 0.1	μΑ
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> = - 10V, I <sub>C</sub> = - 10mA	40		320	C. C.
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = -20 \text{mA}, I_B = -2 \text{mA}$		77.14	- 0.6	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_C = -20 \text{mA}, I_B = -2 \text{mA}$		M	- 1	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = -30V, I_{C} = -10mA$		150		MHz
C <sub>ob</sub>	Output Capacitance	$V_{CB} = -30V$ , $f = 1MHz$		3.1		pF
C <sub>re</sub>	Reverse Transfer Capacitance	V <sub>CB</sub> = - 30V, f = 1MHz		2.3		pF

# h<sub>FE</sub> Classification

Classification	С	D	E	F
h <sub>FE</sub>	40 ~ 80	60 ~ 120	100 ~ 200	160 ~ 320

# **Typical Characteristics**

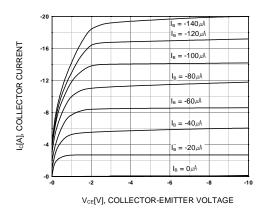


Figure 1. Static Characteristic

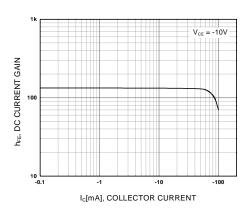


Figure 3. DC current Gain

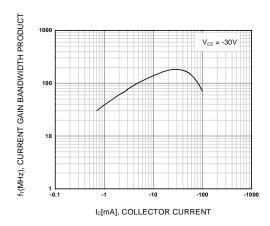
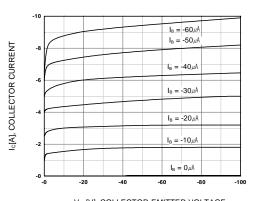


Figure 5. Current Gain Bandwidth Product



 $V_{\text{CE}}[V], \, \text{COLLECTOR-EMITTER} \, \, \text{VOLTAGE}$ 

Figure 2. Static Characteristic

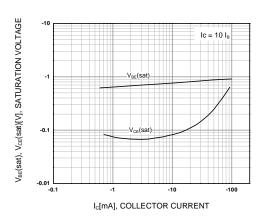


Figure 4. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

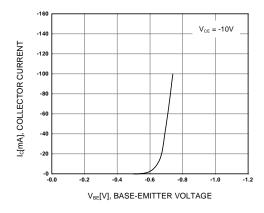


Figure 6. Base-Emitter On Voltage

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# Typical Characteristics (Continued)

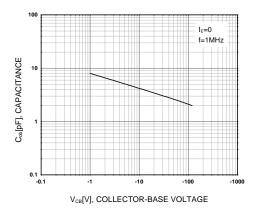


Figure 7. Collector Output Capacitance

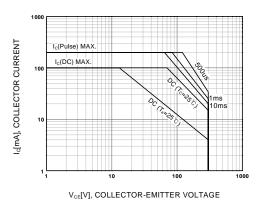


Figure 9. Safe Operating Area

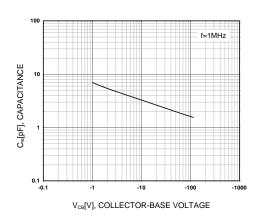


Figure 8. Reverse Transfer Capacitance

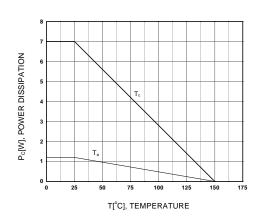
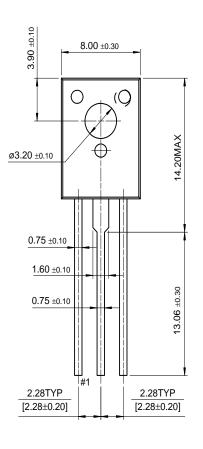


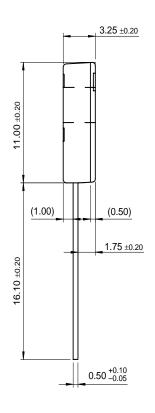
Figure 10. Power Derating

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# **Package Demensions**

TO-126







Dimensions in Millimeters

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